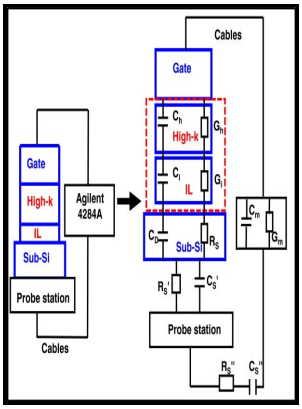
Characterization of Gd2O3 high-K dielectric films on Si(001)

National Library of Canada - A comprehensive study on usage of Gd2O3 dielectric in MOS based radiation sensors considering frequency dependent radiation response



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-
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Canadian theses = -- Thèses canadiennesCharacterization of Gd2O3 high-K dielectric films on Si(001)
Notes: Thesis (M.A.Sc.) -- University of Toronto, 2000.
This edition was published in 2000

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Phase control of magnetron sputtering deposited Gd2O3 thin films as high

Osten: Charge trapping in ultrathin Gd 2O 3 high- k dielectric. Substantial reduction of the leakage current density and disappearance of hysteresis…. Haukka: Physical and electrical properties of Zr-silicate dielectric layers deposited by atomic layer deposition.

Improving dielectric properties of epitaxial Gd2O3 thin films on silicon by nitrogen doping

Substitutional nitrogen incorporation into the dielectric layer was confirmed by secondary ion mass spectroscopy and X-ray photoelectron spectroscopy analysis.

Characterization of gadolinium oxide film by pulse laser deposition

Behnke Paul-Drude-Institute, Berlin for the technical support during the experiment and BESSY II Helmholtz-Zentrum, Berlin for granting the beamtime under project 100876.

Growth of Crystalline Gd2O3 Thin Films with a High

Mogul: Thermochemical description of dielectric breakdown in high dielectric constant materials. Bailey: Characterization of hafnium aluminate gate dielectrics deposited by liquid injection metalorganic chemical vapor deposition. Waser: Oxygen vacancy migration and time-dependent leakage current behavior of Ba 0.

Delayed crystallization of ultrathin Gd2O3 layers on Si(111) observed by in situ X

European Journal of Inorganic Chemistry 2010, 2010 31 , 4952-4961. The radiation response of the Gd 2O 3 MOS capacitors was investigated by 60Co irradiation in the range of 0.

Characterization of gadolinium oxide film by pulse laser deposition

In addition, both interface at Si and Ni fully silicide FUSI gate were smooth without the formation of Si-oxide. Waghmare: Effects of O vacancies and C doping on dielectric properties of ZrO 2: A first-principles study. After that, the as-cleaned wafers were loaded into the MBE growth chamber with a base pressure of 7.

Molecular beam epitaxy deposition of Gd2O3 thin films on SrTiO3 (100) substrate

Homoleptic Gadolinium Amidinates as Precursors for MOCVD of Oriented Gadolinium Nitride GdN Thin Films.

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